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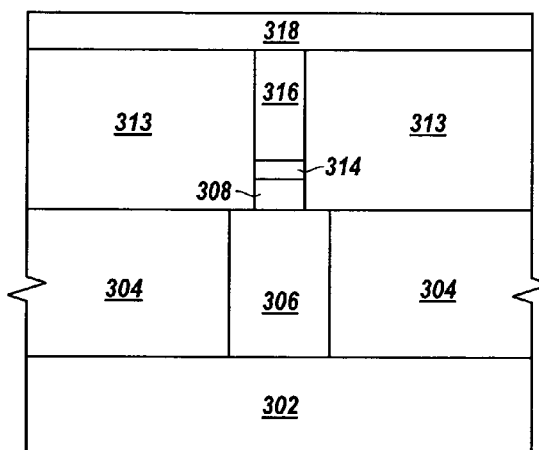


Fig. 3

(57) Abstract: Methods, devices, and systems associated with phase change memory structures are described herein. One method of forming a phase change memory structure includes forming an insulator material on a first conductive element and on a dielectric material of a phase change memory cell, forming a heater self-aligned with the first conductive element, forming a phase change material on the heater and at least a portion of the insulator material formed on the dielectric material, and forming a second conductive element of the phase change memory cell on the phase change material.

